WTM303N040LS-HAF

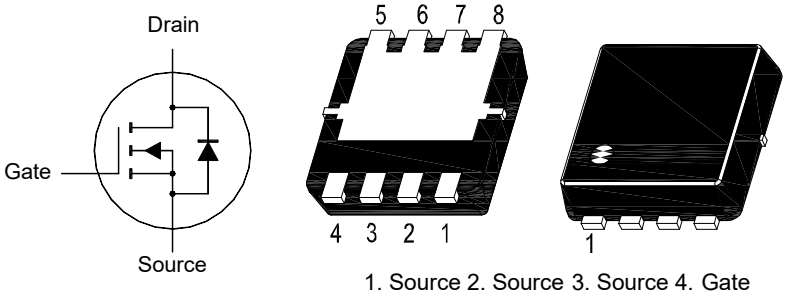
N-Channel Enhancement Mode MOSFET

Features

- Low $R_{DS(ON)}$
- Low Gate Charge
- Halogen and Antimony Free(HAF), RoHS compliant

Application

- Motor/Body Load Control
- Load Switch
- DC-DC converters and Off-line UPS



1. Source 2. Source 3. Source 4. Gate
5. Drain 6. Drain 7. Drain 8. Drain
DFN3030 Plastic Package

Key Parameters

Parameter	Value	Unit
BV_{DSS}	30	V
$R_{DS(ON)}$ Max	4 @ V_{GS} = 10 V	mΩ
	5.5 @ V_{GS} = 4.5 V	
$V_{GS(th)}$ typ	1.5	V
Q_g typ	53 @ V_{GS} = 10 V	nC

Absolute Maximum Ratings (at T_a = 25℃ unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	T_c = 25℃	I_D	48	A
	T_c = 100℃		30	
Peak Drain Current, Pulsed [1]		I_{DM}	280	A
Avalanche Current		I_{AS}	33	A
Single Pulse Avalanche Energy [2]		E_{AS}	54.5	mJ
Power Dissipation	T_c = 25℃	P_{tot}	15.6	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	℃

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	8	℃/W
Thermal Resistance from Junction to Ambient [3]	$R_{\theta JA}$	50	℃/W

[1] Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 2%, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ = 150°C.

[2] Limited by $T_{J(MAX)}$, starting T_J = 25 °C, L = 0.1 mH, R_g = 25 Ω, I_D = 33 A, V_{GS} = 10 V.

[3] Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at T_a = 25℃ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at I_D = 250 μA	BV_{DSS}	30	-	-	V
Drain-Source Leakage Current at V_{DS} = 30 V	I_{DSS}	-	-	1	μA
Gate Leakage Current at V_{GS} = ± 20 V	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at V_{DS} = V_{GS}, I_D = 250 μA	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at V_{GS} = 10 V, I_D = 24 A at V_{GS} = 4.5 V, I_D = 12 A	$R_{DS(on)}$	- -	3.2 -	4 5.5	mΩ
DYNAMIC PARAMETERS					
Gate resistance at V_{DS} = 0 V, f = 1 MHz	R_g	-	1	-	Ω
Forward Transconductance at V_{DS} = 5 V, I_D = 24 A	g_{fs}	-	27	-	S
Input Capacitance at V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz	C_{iss}	-	2300	-	pF
Output Capacitance at V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz	C_{oss}	-	278	-	pF
Reverse Transfer Capacitance at V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz	C_{rss}	-	229	-	pF
Gate charge total at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 10 V at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 4.5 V	Q_g	- -	53 26	- -	nC
Gate to Source Charge at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 10 V	Q_{gs}	-	8.5	-	nC
Gate to Drain Charge at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 10 V	Q_{gd}	-	13	-	nC
Turn-On Delay Time at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 10 V, R_g = 3.3 Ω	$t_{d(on)}$	-	18	-	ns
Turn-On Rise Time at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 10 V, R_g = 3.3 Ω	t_r	-	54	-	ns
Turn-Off Delay Time at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 10 V, R_g = 3.3 Ω	$t_{d(off)}$	-	18	-	ns
Turn-Off Fall Time at V_{DS} = 15 V, I_D = 24 A, V_{GS} = 10 V, R_g = 3.3 Ω	t_f	-	7	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at I_S = 1 A, V_{GS} = 0 V	V_{SD}	-	-	1.2	V
Body-Diode Continuous Current	I_S	-	-	48	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	280	A
Body Diode Reverse Recovery Time at I_S = 24 A, di/dt = 100 A / μs	t_{rr}	-	15.5	-	ns
Body Diode Reverse Recovery Charge at I_S = 24 A, di/dt = 100 A / μs	Q_{rr}	-	6.4	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristic

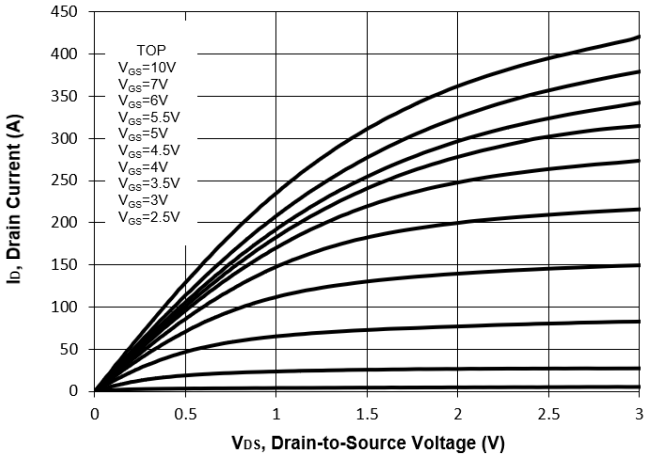


Fig. 2 Typical Transfer Characteristic

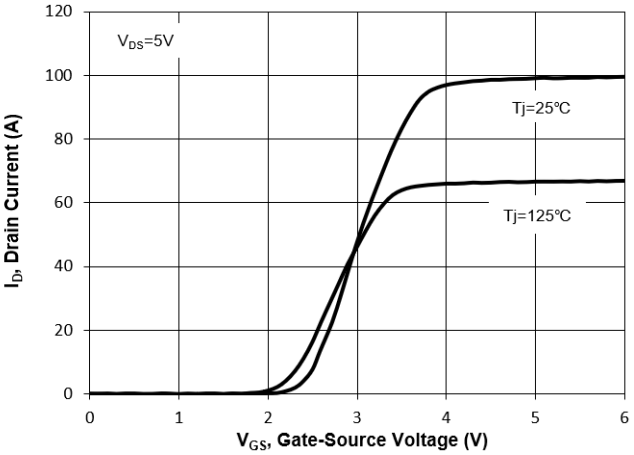


Fig. 3 on-Resistance vs. Drain Current

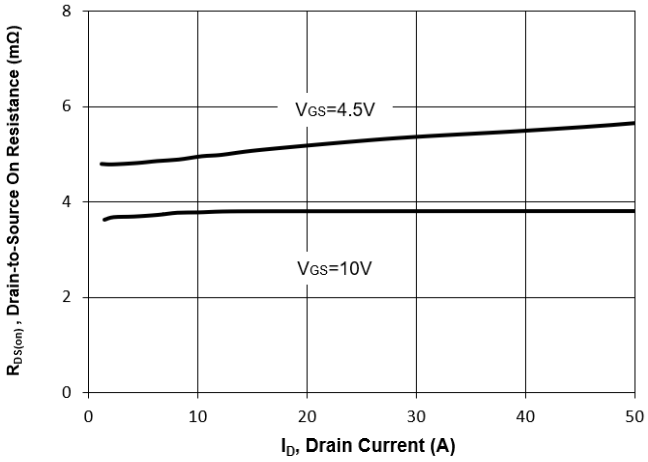


Fig. 4 on-Resistance vs. Gate Voltage

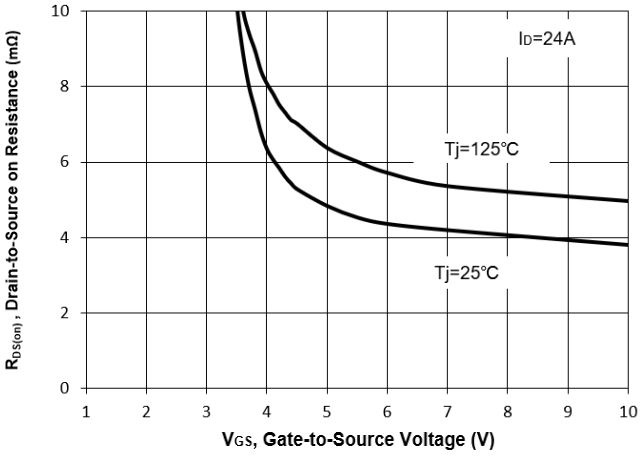


Fig. 5 on-Resistance vs.T_j

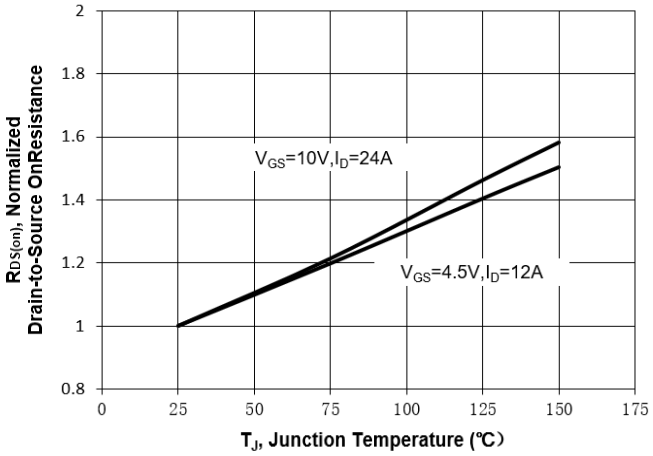
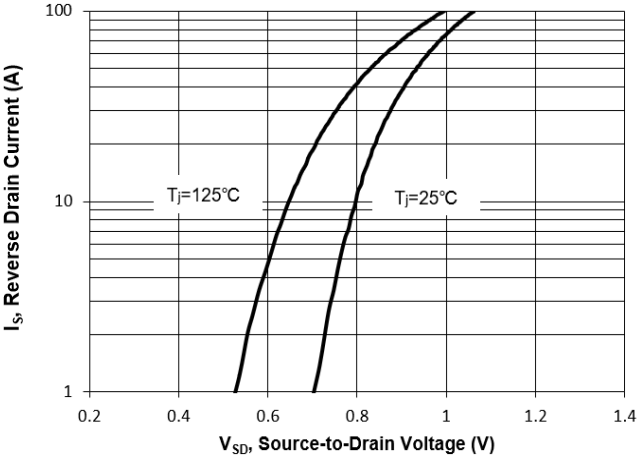


Fig. 6 Typical Body-Diode Forward Characteristic



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

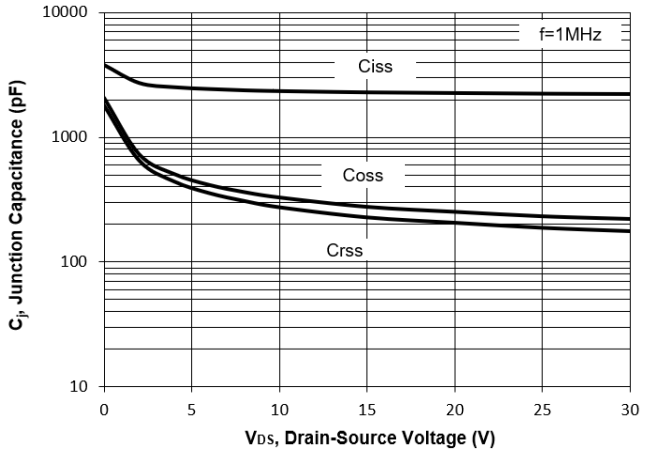


Fig. 8 Drain-Source Leakage Current vs. T_j

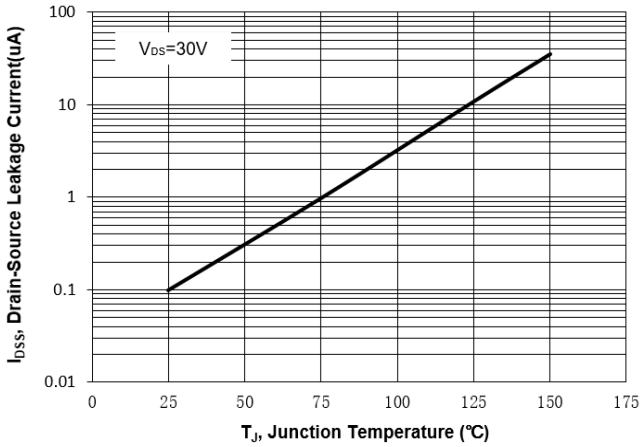


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

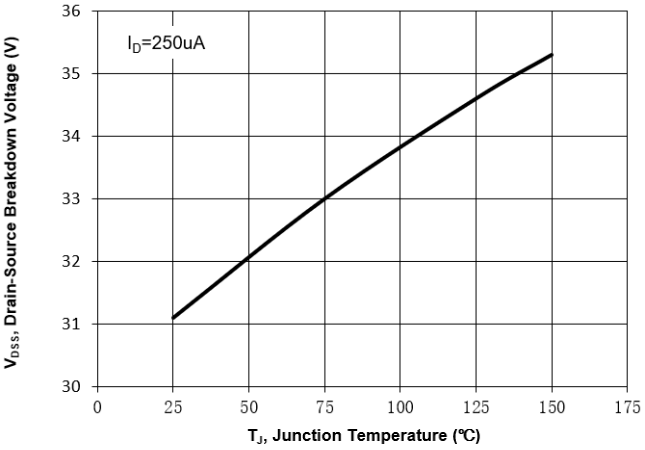


Fig. 10 Gate Threshold Variation vs. T_j

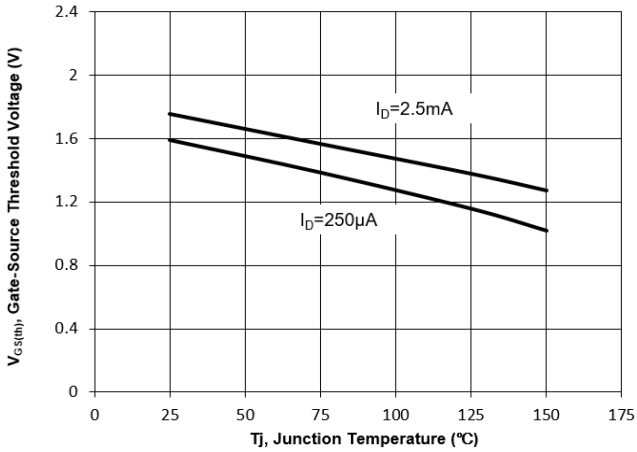


Fig. 11 Gate Charge

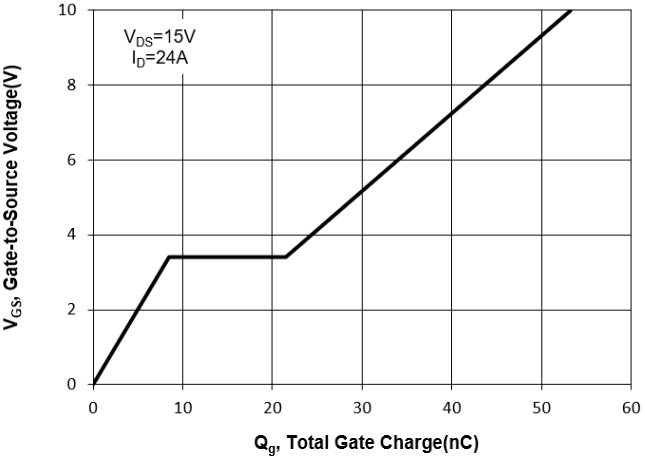
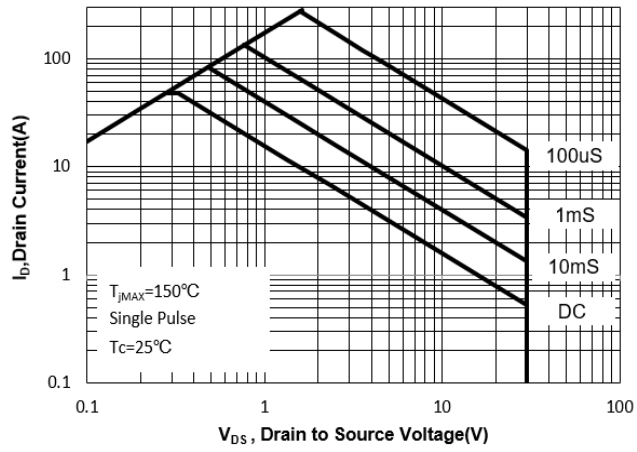


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($z_{\Theta JC}$)

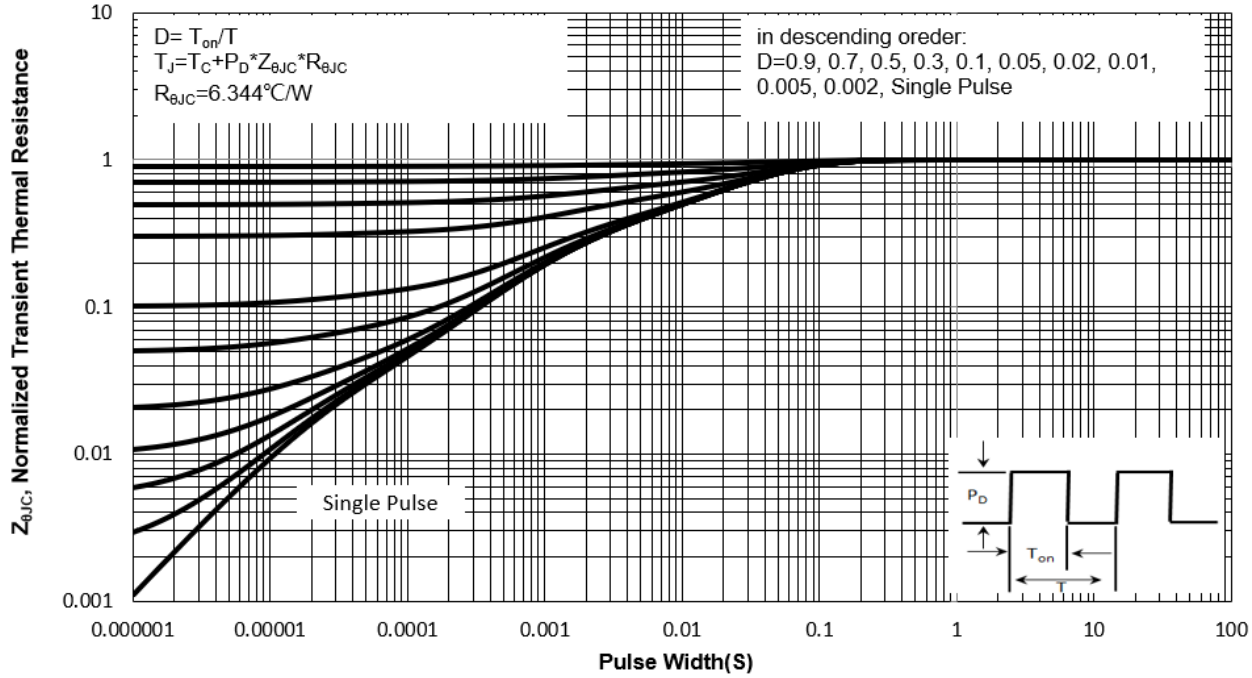
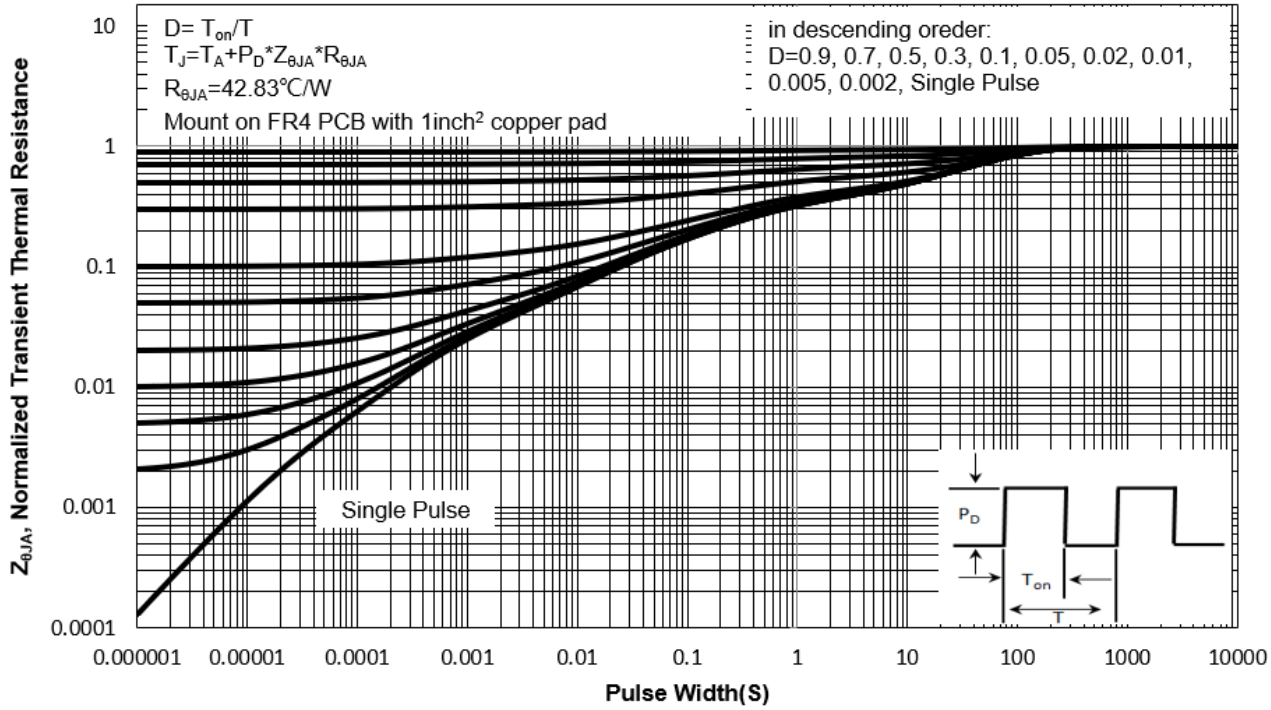


Fig. 14 Normalized Maximum Transient Thermal Impedance($z_{\Theta JA}$)



Test Circuits

Fig.1-1 Switching times test circuit

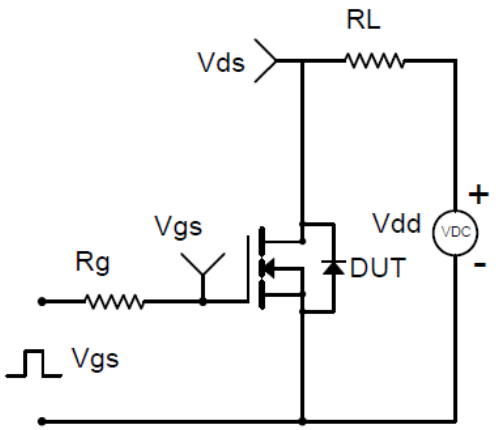


Fig.1-2 Switching Waveform

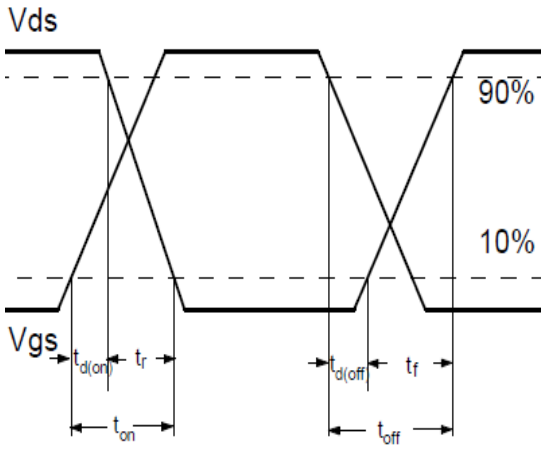


Fig.2-1 Gate charge test circuit

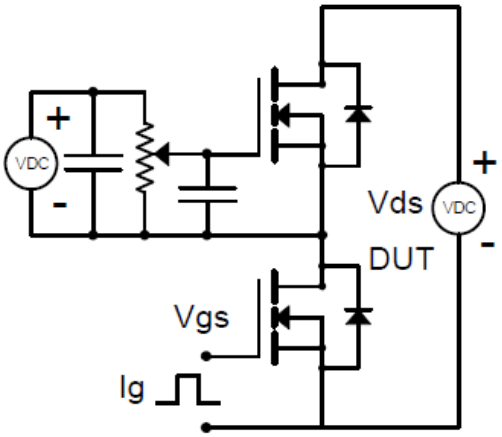


Fig.2-2 Gate charge waveform

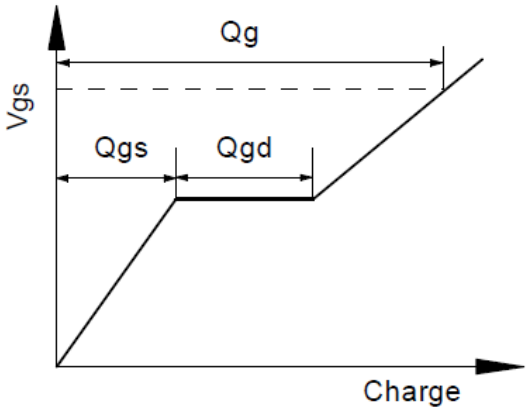


Fig.3-1 Avalanche test circuit

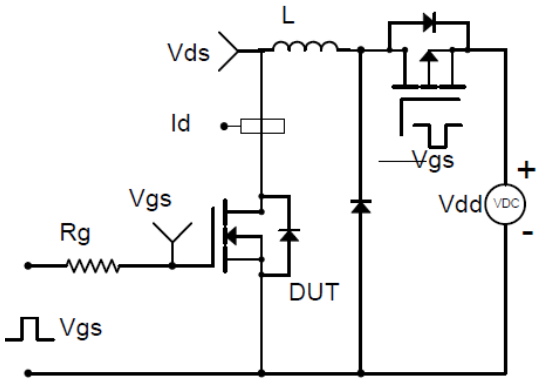
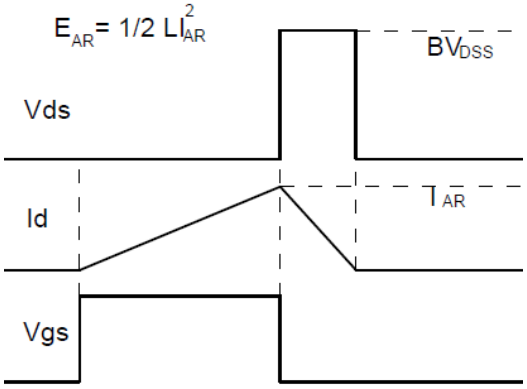
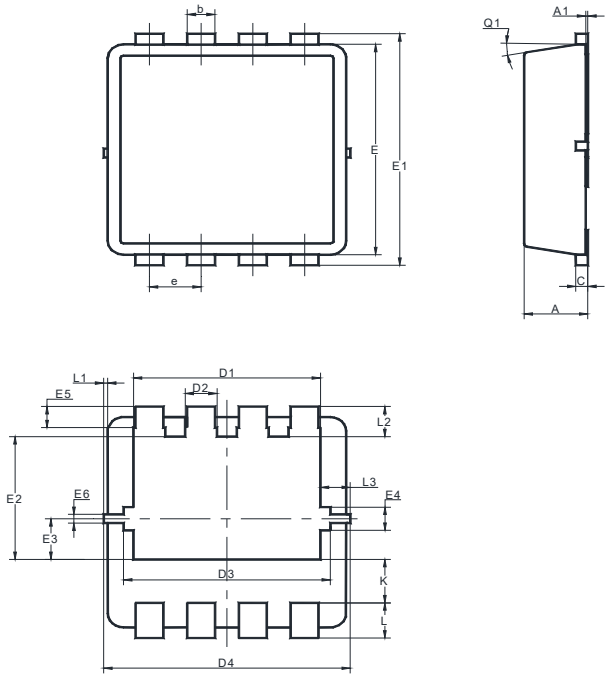


Fig.3-2 Avalanche waveform



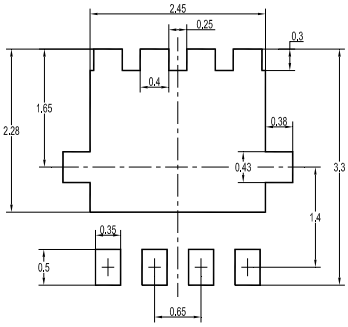
Package Outline Dimensions (Units: mm) DFN3030



UNIT	A	A1	b	c	D1	D2	D3	D4	E	E1	E2	E3	E4
mm	0.9	0.05	0.35	0.25	2.6	0.5	2.7	3.2	3.1	3.3	1.85	0.68	0.43
	0.7	0	0.24	0.1	2.4	0.3	2.5	3	2.9	3.1	1.65	0.48	0.23

UNIT	E5	E6	e	K	L	L1	L2	L3	θ1
mm	0.4	0.25	0.7	0.72	0.5	0.1	0.53	0.475	12°
	0.2	0.15	0.6	0.52	0.3	0	0.33	0.275	0°

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN3030	12	8 ± 0.1	0.315 ± 0.004	330	13	5,000

Marking information

" TM303N040LS " = Part No.

" ****** " = Date Code Marking

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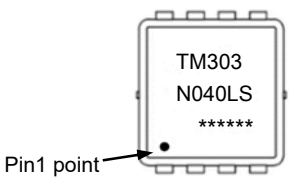

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